





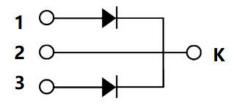
S3D10065E2 650V SIC POWER SCHOTTKY RECTIFIER



Description

S3D10065E2 is a SiC Schottky rectifier packaged in DPAK(TO-252-2) case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D10065E2 is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-		
Working Peak Reverse Voltage	V _{RWM}		650	V
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F (AV)}	Tc=150°C	5 (per leg) 10 (per device)	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	10ms, Half Sine pulse, T _J =25°C	70(per leg)	Α
Repetitive Peak Forward Surge Current	I_{FRM}	10 ms, Half Sine pulse , T _J =25°C	30(per leg)	Α
Non-Repetitive Peak Forward Surge Current	I _{F,Max}	10μs. Pulse, Tյ=25℃	700(per leg)	А
Power Dissipation	P _{tot}	T _J =25℃	103(per leg)	W

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 5A, Pulse, T _J = 25 °C	1.4	1.7	٧
	V_{F2}	@ 5A, Pulse, T _J = 175 °C	1.6	2.4	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.002	8	uA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 175 ^{\circ}\text{C}$	0.06	25	uA
Junction Capacitance	Ст	V _R =0V, T _J =25℃, f=1MHz	382	-	pF
Reverse Recovery Charge	Qc	$I_F = 6A$, di/dt = 500A/ μ s VR = 400 V, T _J =25°C	23.8	ı	nC
Capacitance Stored Energy	E c	V _R = 400 V	5.88	-	μJ

^{*} Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to	R ₀ JC	DC operation	3.0(per leg)	°C/W
Case			1.5(both leg)	C/VV

Marking Diagram



Where XXXXX is YYWWL

S3D = Device Type E2 = Package type

10 = Forward Current (10A) 065 = Reverse Voltage (650V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
S3D10065E2	DPAK(TO-252-2)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.







Ratings and Characteristics Curves (per leg)

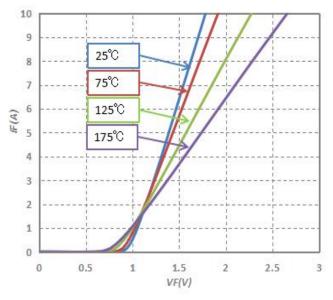


Fig.1-Typical Forward Voltage Characteristics

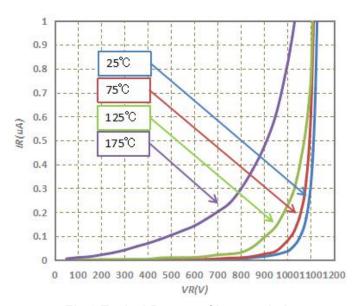


Fig.2-Typical Reverse Characteristics

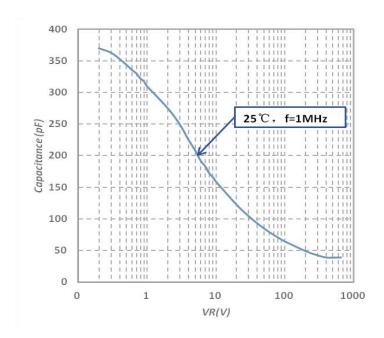


Fig.3-Capacitance vs. Reverse Voltage

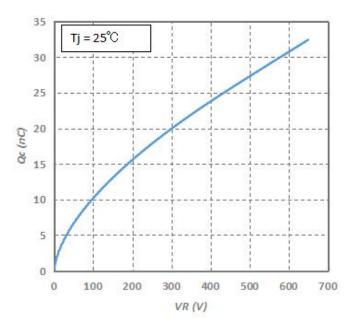
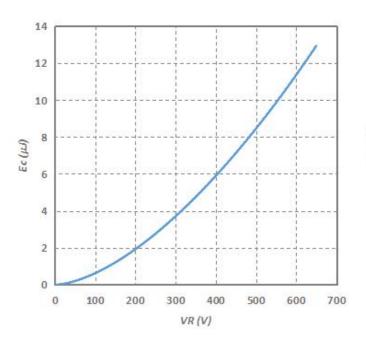


Fig.4-Total Capacitance Charge vs. Reverse Voltage









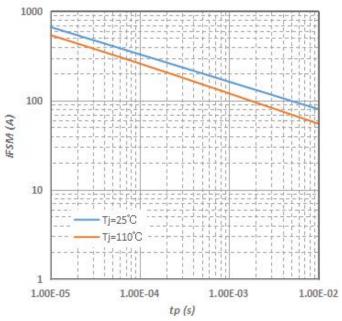
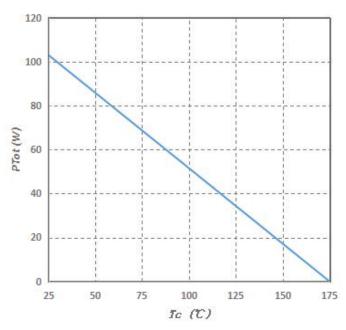


Fig.5-Capacitance Stored Energy

Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)





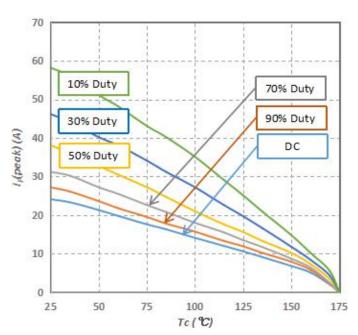


Fig.8-Current Derating

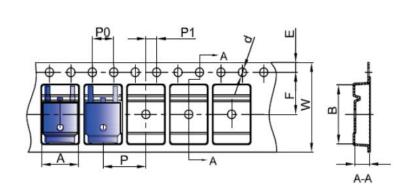
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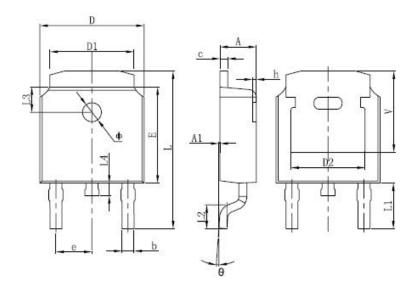


Carrier Tape & Reel Specification DPAK(TO-252-2)



SYMBOL	Millimeters		
STWBOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
Е	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

Mechanical Dimensions DPAK(TO-252-2)



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	2.20	2.40	0.086	0.094	
A1	0	0.13	0	0.005	
b	0.635	0.889	0.025	0.035	
С	0.460	0.889	0.018	0.035	
D	6.50	6.70	0.250	0.265	
D1	4.95	5.46	0.195	0.215	
D2	4.32	REF.	0.170 REF.		
E	6.00	6.20	0.235	0.245	
е	2.286	BSC	0.090 BSC		
L	9.398	10.414	0.370	0.410	
L1	1.778	1.778 REF.		0.108 REF.	
L2	1.40	1.78	0.055	0.07	
L3	1.60 REF.		0.063 REF.		
L4	0.60	1.02	0.024	0.040	
Ф	1.10	1.30	0.043	0.051	
Θ	0°	10°	0°	10°	
h	0	0.30	0	0.012	
V	5.21 REF.		0.205	REF.	







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